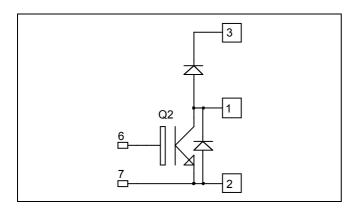


Boost chopper NPT IGBT Power Module

$$V_{CES} = 600V$$

 $I_{C} = 330A$ @ $T_{C} = 80^{\circ}C$



Application • AC

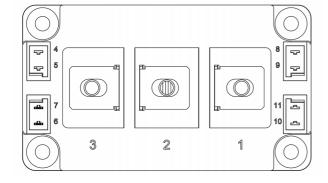
- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Non Punch Through (NPT) FAST IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant



Absolute maximum ratings

| Symbol | Parameter | | Max ratings | Unit |
|-------------|---------------------------------------|----------------------|-------------|------|
| V_{CES} | Collector - Emitter Breakdown Voltage | | 600 | V |
| $I_{\rm C}$ | Continuous Collector Current | $T_C = 25^{\circ}C$ | 520 | |
| | Continuous Conector Current | $T_C = 80$ °C | 330 | A |
| I_{CM} | Pulsed Collector Current | $T_C = 25^{\circ}C$ | 800 | |
| V_{GE} | Gate – Emitter Voltage | | ±20 | V |
| P_{D} | Maximum Power Dissipation | $T_C = 25$ °C | 1560 | W |
| RBSOA | Reverse Bias Safe Operating Area | $T_j = 125^{\circ}C$ | 800A @ 520V | |

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

| Symbol | Characteristic | Test Conditions | | Min | Тур | Max | Unit |
|----------------------|--------------------------------------|---|---------------------|-----|------|------|------|
| I_{CES} | Zero Gate Voltage Collector Current | $V_{GE} = 0V, V_{CE} = 600V$ | | | | 500 | μA |
| V _{CE(sat)} | Collector Emitter saturation Voltage | , GE 10 , | $T_j = 25^{\circ}C$ | | 1.95 | 2.45 | V |
| | | | $T_j = 125$ °C | | 2.2 | | · |
| $V_{GE(th)}$ | Gate Threshold Voltage | $V_{GE} = V_{CE}, I_C = 7.5 \text{ mA}$ | | 5.0 | 5.8 | 6.5 | V |
| I_{GES} | Gate – Emitter Leakage Current | $V_{GE} = 20V, V_{CE} = 0V$ | | | | 1200 | nA |

Dynamic Characteristics

| Symbol | Characteristic | Test Conditions | | Min | Тур | Max | Unit |
|------------------|------------------------------|--|----------------|-----|------|-----|------|
| Cies | Input Capacitance | $V_{GE} = 0V ; V_{CE} = 25V$ $f = 1MHz$ | | | 18 | | nF |
| C_{res} | Reverse Transfer Capacitance | | | | 1.6 | | |
| Q_{G} | Gate charge | V _{GE} =15V, I _C =400A V _{CE} =300V | | | 1.3 | | μС |
| $T_{d(on)}$ | Turn-on Delay Time | Inductive Switch | ing (25°C) | | 150 | | |
| $T_{\rm r}$ | Rise Time | $V_{GE} = \pm 15V$ | | | 72 | | |
| $T_{d(off)}$ | Turn-off Delay Time | $V_{\text{Bus}} = 300V$ $I_{\text{C}} = 400A$ $R_{\text{G}} = 8\Omega$ | | | 530 | | ns |
| T_{f} | Fall Time | | | | 40 | | |
| $T_{d(on)}$ | Turn-on Delay Time | Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_{C} = 400A$ $R_{G} = 8\Omega$ | | | 160 | | ns |
| T_{r} | Rise Time | | | | 75 | | |
| $T_{d(off)}$ | Turn-off Delay Time | | | | 550 | | |
| $T_{\rm f}$ | Fall Time | | | | 50 | | |
| Eon | Turn on Energy | $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ | $T_j = 125$ °C | | 18 | | mJ |
| E_{off} | Turn off Energy | $I_{C} = 400A$ $R_{G} = 8\Omega$ | $T_j = 125$ °C | | 17 | | 1110 |
| I_{sc} | Short Circuit data | $V_{GE} \le 15V$; $V_{Bus} = 360V$ $t_p \le 10 \mu s$; $T_i = 125 ^{\circ}C$ | | | 1800 | | A |

Reverse diode ratings and characteristics

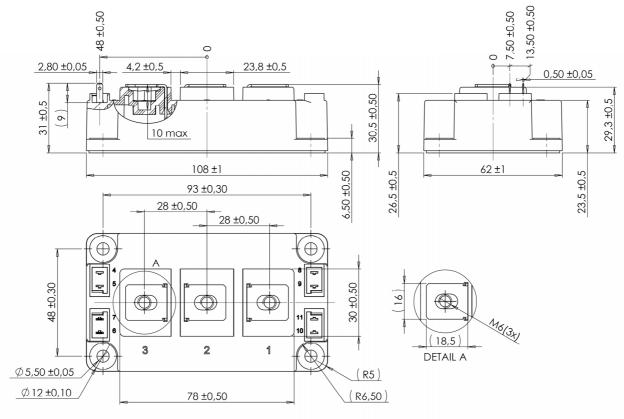
| Symbol | Characteristic | Test Conditions | | Min | Typ | Max | Unit |
|------------------|---|---|---|-----|------|------|------|
| V_{RRM} | Maximum Peak Repetitive Reverse Voltage | | | 600 | | | V |
| I_{RRM} | Maximum Reverse Leakage Current | $V_R = 600V$ | $T_i = 25^{\circ}C$ | | | 750 | μΑ |
| I_{F} | DC Forward Current | | $T_{j} = 125^{\circ}C$ $Tc = 80^{\circ}C$ | | 400 | 1000 | A |
| V | Diode Forward Voltage | $I_F = 400A$ $V_{GE} = 0V$ | $T_i = 25^{\circ}C$ | | 1.25 | 1.6 | V |
| V_{F} | | | $T_i = 125^{\circ}C$ | | 1.2 | | |
| + | Reverse Recovery Time | $I_F = 400A$ $V_R = 300V$ $di/dt = 4400A/\mu s$ | $T_j = 25^{\circ}C$ | | 150 | | ns |
| t_{rr} | | | $T_j = 125$ °C | | 250 | | |
| Q _{rr} | Reverse Recovery Charge | | $T_i = 25^{\circ}C$ | | 27 | | |
| | | | $T_j = 125$ °C | | 44 | | μC |
| E _{rr} | Reverse Recovery Energy | αι/αι 1100/1/μ3 | $T_i = 25^{\circ}C$ | | 5.6 | | ma T |
| | | | $T_{i} = 125^{\circ}C$ | | 9.2 | | mJ |



Thermal and package characteristics

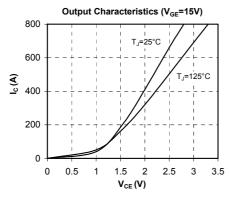
| Symbol | Characteristic | | | Min | Тур | Max | Unit |
|---|--|--------------------------------------|------|------|-----|------|--------|
| D | Junction to Case Thermal Resistance | | IGBT | | | 0.08 | °C/W |
| R _{thJC} Junction to Case Thermal Resistan | | Diode | | | | 0.15 | C/ VV |
| V_{ISOL} | RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz | | | 4000 | | | V |
| T_{J} | Operating junction temperature range | Operating junction temperature range | | -40 | | 150 | |
| T_{STG} | Storage Temperature Range | | -40 | | 125 | °C | |
| $T_{\rm C}$ | Operating Case Temperature | | | -40 | | 125 | |
| Torque | Mounting forque | For terminals | M6 | 3 | | 5 | N.m |
| | | To Heatsink | M6 | 3 | | 5 | 18.111 |
| Wt | Package Weight | | | | | 350 | g |

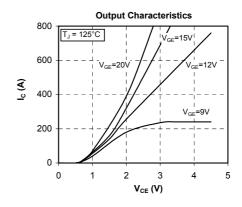
D3 Package outline (dimensions in mm)

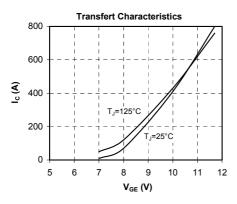


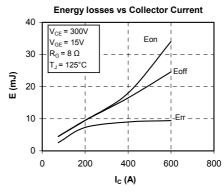


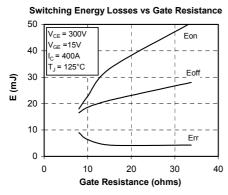
Typical Performance Curve

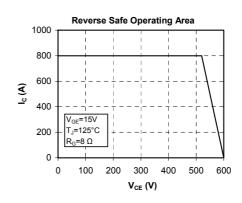


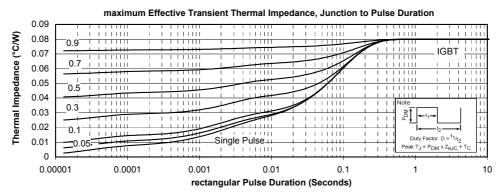








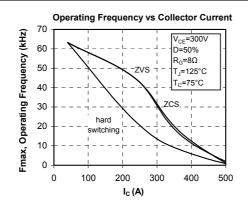


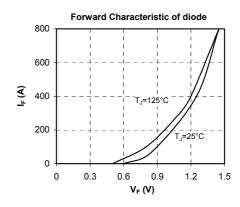


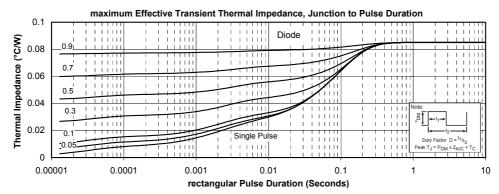
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